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Extreme Ultraviolet (EUV) Lithography VIII

**Eric M. Panning
Kenneth A. Goldberg**
Editors

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Contents

ix	<i>Authors</i>
xiii	<i>Conference Committee</i>

KEYNOTE SESSION

10143 06	Progress in EUV lithography toward manufacturing (Keynote Paper) [10143-2]
----------	---

EUV MATERIALS I: METAL-BASED EUV RESISTS: JOINT SESSION WITH CONFERENCES 10146 AND 10143

10143 08	Nanoparticle photoresist studies for EUV lithography [10143-4]
10143 09	Advanced development techniques for metal-based EUV resists [10143-5]

EUV MATERIALS II: FUNDAMENTALS I: JOINT SESSION WITH CONFERENCES 10146 AND 10143

10143 0A	Absorption coefficient and exposure kinetics of photoresists at EUV [10143-6]
10143 0B	Correlation of experimentally measured atomic scale properties of EUV photoresist to modeling performance: an exploration [10143-7]

INTEGRATION

10143 0D	Enabling sub-10nm node lithography: presenting the NXE:3400B EUV scanner (Invited Paper) [10143-9]
10143 0E	Line-edge roughness performance targets for EUV lithography [10143-10]
10143 0F	Mix-and-match considerations for EUV insertion in N7 HVM [10143-11]
10143 0G	The future of EUV lithography: enabling Moore's Law in the next decade [10143-12]
10143 0H	SAQP and EUV block patterning of BEOL metal layers on IMEC's iN7 platform [10143-13]
10143 0I	Modeling EUVL patterning variability for metal layers in 5nm technology node and its effect on electrical resistance [10143-14]

**EUV MASK INSPECTION AND IMAGING: JOINT SESSION WITH CONFERENCES
10143 AND 10145**

10143 OJ **Actinic review of EUV masks: performance data and status of the AIMS EUV system**
[10143-15]

10143 OK **Printability and actinic AIMS review of programmed mask blank defects** [10143-16]

EUV OPTICS AND PELLICLE

10143 OL **Novel membrane solutions for the EUV pellicle: better or not?** [10143-17]

10143 OM **Impact of tool design on defect detection sensitivity for EUV actinic blank inspection**
[10143-18]

10143 ON **High-NA metrology and sensing on Berkeley MET5** [10143-19]

10143 OP **Investigating surface structures by EUV scattering** [10143-21]

RESIST ADVANCES AND INTEGRATION

10143 OQ **Improvements in resist performance towards EUV HVM (Invited Paper)** [10143-22]

10143 OR **Exploring the readiness of EUV photo materials for patterning advanced technology nodes**
[10143-23]

10143 OT **State-of-the-art EUV materials and processes for the 7nm node and beyond** [10143-25]

10143 OU **High-volume manufacturing compatible dry development rinse process (DDRP): patterning
and defectivity performance for EUVL** [10143-26]

10143 OV **Sensitivity enhancement of the high-resolution xMT multi-trigger resist for EUV lithography**
[10143-27]

RESIST MODELING

10143 OW **Mechanisms of EUV exposure: electrons and holes** [10143-28]

10143 OY **Driving down defect density in composite EUV patterning film stacks** [10143-30]

10143 OZ **Lithographic stochastics: beyond 3σ** [10143-31]

MASKS I

10143 IO **Reducing EUV mask 3D effects by alternative metal absorbers** [10143-32]

- 10143 11 **N7 dark field two-bar in 0.33NA EUVL: Mitigation of CD Bossung tilts caused by strong coupling between the feature's primary and 1st self-image** [10143-33]
- 10143 12 **Investigation of alternate mask absorbers in EUV lithography** [10143-34]
- 10143 13 **Vote-taking for EUV lithography: a radical approach to mitigate mask defects** [10143-35]
- 10143 14 **Reticle enhancement techniques toward iN7 metal2** [10143-36]

MASKS II

- 10143 15 **Considerations for pattern placement error correction toward 5nm node** [10143-37]
- 10143 16 **Enabling full field physics based OPC via dynamic model generation** [10143-39]
- 10143 17 **Rigorous 3D electromagnetic simulation of ultrahigh efficiency EUV contact-hole printing with chromeless phase shift mask** [10143-40]

PATTERNING I

- 10143 18 **Single exposure EUV patterning of BEOL metal layers on the IMEC iN7 platform (Invited Paper)** [10143-41]
- 10143 19 **Integrated approach to improving local CD uniformity in EUV patterning** [10143-42]
- 10143 1A **Comprehensive analysis of line-edge and line-width roughness for EUV lithography** [10143-43]
- 10143 1C **New methodologies for lower-K1 EUV OPC and RET optimization** [10143-45]
- 10143 1D **Ultrathin EUV patterning stack using polymer brush as an adhesion promotion layer** [10143-46]

PATTERNING II

- 10143 1E **Compact 2D OPC modeling of a metal oxide EUV resist for a 7nm node BEOL layer** [10143-47]
- 10143 1F **Minimizing wafer overlay errors due to EUV mask non-flatness and thickness variations for N7 production** [10143-48]
- 10143 1G **Single-expose patterning development for EUV lithography** [10143-49]
- 10143 1H **Single-nm resolution approach by applying DDRP and DDRM** [10143-50]

SOURCE

- 10143 1J **Performance of 250W high-power HVM LPP-EUV source** [10143-52]

POSTERS: INSPECTION

- 10143 1N **First light at EBL2** [10143-56]
- 10143 1O **RESCAN: an actinic lensless microscope for defect inspection of EUV reticles** [10143-57]
- 10143 1P **Arc-shaped slit effect of EUV lithography with anamorphic high-NA system in terms of critical dimension variation** [10143-58]
- 10143 1Q **A two-step method for fast and reliable EUV mask metrology** [10143-59]

POSTERS: MASKS AND OPTICS/PELLICLE

- 10143 1S **Monte Carlo sensitivity analysis of EUV mask reflectivity and its impact on OPC accuracy** [10143-61]
- 10143 1T **A study on EUV reticle surface molecular contamination under different storage conditions in a HVM foundry fab** [10143-62]
- 10143 1U **CD error caused by aberration and its possible compensation by optical proximity correction in extreme-ultraviolet lithography** [10143-63]
- 10143 1V **Impact of non-uniform wrinkles for a multi-stack pellicle in EUV lithography** [10143-64]
- 10143 1W **Image-based pupil plane characterization for anamorphic lithography systems** [10143-89]

POSTERS: PRINTING

- 10143 1Y **Contribution of EUV mask CD variability on LCDU** [10143-66]
- 10143 1Z **EUV process improvement with novel litho track hardware** [10143-67]
- 10143 20 **Impact of EUV SRAF on Bossung tilt** [10143-68]
- 10143 21 **2D self-aligned via patterning strategy with EUV single-exposure in 3nm technology** [10143-90]

POSTERS: RESIST

- 10143 22 **A study on enhancing EUV resist sensitivity** [10143-69]
- 10143 23 **Impact of acid statistics on EUV local critical dimension uniformity** [10143-70]

- 10143 24 **Influence of post exposure bake time on EUV photoresist RLS trade-off** [10143-71]
- 10143 25 **Extreme ultraviolet patterning of tin-oxo cages** [10143-72]
- 10143 26 **Technology for defectivity improvement in resist coating and developing process in EUV lithography process** [10143-73]
- 10143 27 **In-situ measurement of outgassing generated from EUV resist including metal oxide nanoparticles during electron irradiation** [10143-74]
- 10143 28 **Irresistible Materials multi-trigger resist: the journey towards high volume manufacturing readiness** [10143-75]
- 10143 29 **Simulation and experimentation of PSCAR chemistry for complex structures** [10143-76]
- 10143 2B **Optimization of stochastic EUV resist models parameters to mitigate line edge roughness** [10143-78]
- 10143 2C **Contrast curves for low energy electron exposures of an EUV resist in a scanning electron microscope** [10143-79]
- 10143 2E **Computational approach on PEB process in EUV resist: multi-scale simulation** [10143-91]

POSTERS: SOURCE

- 10143 2G **Key components technology update of the 250W high-power LPP-EUV light source** [10143-83]
- 10143 2I **Study of Sn removal by surface wave plasma for source cleaning** [10143-85]
- 10143 2J **Background pressure effects on EUV source efficiency and produced debris characteristics** [10143-86]
- 10143 2K **Improvement of power, efficiency, and cost of ownership in the tin LPP EUV source** [10143-88]

Authors

Numbers in the index correspond to the last two digits of the seven-digit citation identifier (CID) article numbering system used in Proceedings of SPIE. The first five digits reflect the volume number. Base 36 numbering is employed for the last two digits and indicates the order of articles within the volume. Numbers start with 00, 01, 02, 03, 04, 05, 06, 07, 08, 09, 0A, 0B...0Z, followed by 10-1Z, 20-2Z, etc.

Abe, Tamotsu, 1J, 2G	Custers, Rolf, 0T, 23
Ackerman, Christian, 0W	De Gendt, Stefan, 24
Adam, Kostas, 16	De Schepper, Peter, 1E
Adelmann, Christoph, 0L	De Silva, Anuja, 0Y, 1D, 1G
Anderson, Chris, 0N	De Simone, Danilo, 0R, 0U, 1E, 23, 24
Arnold, John C., 0Y, 1D, 1G	de Winter, L., 11
Asai, Masaya, 1Z	Decoster, Stefan, 0H
Ayothi, Ramakrishnan, 1D, 1G	Delorme, Maxence, 1E
Baert, R., 18	Demand, Marc, 26
Bailey, Todd, 2B	Denbeaux, Gregory, 0B, 0W
Barouch, Eytan, 1P	Derks, Paul, 0Q, 23
Beique, Genevieve, 1G	Deutz, Alex, 1N
Bekaert, Joost P., 0H, 18, 1E	Di Lorenzo, Paolo, 0H, 15
Benschop, Jos, 0G	Dietzel, Martin, 0J
Beral, Christophe, 0R	Dixit, Girish, 19
Bhattarai, Suchit, 2C	Dredonx, Jeannot, 0G
Biafore, John J., 2B	Drissi, Y., 14
Bilski, Bartosz, 0D	Durrant, Danielle, 0Y
Blanco Carballo, Victor M., 0H, 0I, 0U, 14, 18, 21	D'urzo, Lucia, 0U
Bonam, Ravi, 0K, 1A	Dusa, Mircea, 18, 19
Bosker, Jan-Willem, 0D	Earley, William, 09
Brainard, Robert L., 09, 0W	Edrisi, Arash, 10
Brendler, Andy, 2B	Ekinci, Yasin, 09, 0A, 0Q, 0T, 0V, 1O, 1Q, 25
Bretton, Mary, 1A	Enomoto, Masashi, 26
Bristol, Robert L, 0Z	Erdmann, Andreas, 10
Broman, Par, 0D	Evangelista, Fabrizio, 0D
Brouwer, Albert (Fred) M., 0A, 25	Evanschitzky, Peter, 10
Brunner, Timothy A., 0E, 13, 1F	Fallica, Roberto, 0A, 0T
Buitrago, Elizabeth, 0Q, 0T	Farrell, Richard, 1D
Burkhardt, Martin, 12	Felix, Nelson, M., 0F, 0K, 0Y, 1D, 1G
Capelli, Renzo, 0J, 0K	Fenger, Germain, 16
Carcasi, Michael, 29	Fernández Herrero, Analía, 0P
Carlos, Fonseca, 15	Finders, Jo, 0G, 0Q, 11
Castellanos, Sonia, 0A	Fliervoet, T., 18
Chalykh, Roman, 06	Flynn, Tracy, 0W
Chan, BT, 0U	Fonseca, Carlos, 15
Chandonait, Jonathan, 0B	Foubert, Philippe, 0R, 0U, 26
Chen, Xuemei, 0E, 0F, 1F	Franke, Joern-Holger, 0H
Chen, Yulu, 0K, 1S	Freedman, Daniel A., 09
Chi, Cheng, 1D	Frommhold, Andreas, 0V
Cho, Maenghyo, 2E	Fumar-Pici, Anita, 1E
Choi, Joonmyung, 2E	Furukawa, Tsuyoshi, 1D, 1G
Choi, Suhyeong, 21	Gabor, Allen, 0E, 0F, 1F
Chuang, Steven, 19	Gallagher, Emily E., 0H, 0L, 14, 18
Chunder, Anindarupa, 2B	Gallagher, M., 18
Ciofi, Ivan, 0I, 18	Gao, Weimin, 0I
Clifford, Chris, 16	Giannelis, Emmanuel P., 08
Colsters, Paul, 0H	Gillijns, Werner, 14, 18, 1E
Corliss, Daniel, 0K	Goodwin, Francis, 0K, 1S

Greer, Michael, 1E
 Grzeskowiak, Steven, 0B, 0W
 Gullikson, Eric, 1S
 Guo, Jing, 1D
 Haase, Anton, 0P
 Haitjema, Jarich, 0A, 25
 Halder, S., 18
 Hamieh, Bassem, 1G
 Han, Geng, 13
 Han, Seulgi, 1G
 Hara, Arisa, 15
 Harada, Tetsuo, 22
 Harm, Greg, 19
 Harumoto, Masahiko, 1Z
 Heil, Tilmann, 0G
 Helfenstein, Patrick, 1O, 1Q
 Hellweg, Dirk, 0J, 0K
 Hendrickx, Eric, 0H, 0I, 10, 18
 Hermans, Jan, 19
 Hetel, Iulian, 0U
 Hetzer, Dave, 0Y
 Higgins, Craig, 0E
 Hoefnagels, Rik, 0Q, 0T, 23
 Hollemans, Christiaan, 1N
 Hollink, T., 18
 Hontake, Koichi, 0Y
 Hooker, Kevin, 1C
 Hori, Tsukasa, 1J, 2G
 Hosler, Erik, 0F
 Hotalen, Jodi, 09
 Hsu, Stephen, 11, 20
 Huang, Huai, 1A
 Hubbard, Alex, 0Y
 Huli, Lior, 0Y
 Huyghebaert, Cedric, 0L
 Hwang, Jeong-Gu, 1U
 Hwang, Myungsoo, 06
 Ichinomiya, Hiroshi, 26
 Irmischer, Matthias, 10
 Iseki, Tomohiro, 29
 Jasper, Hans, 0D
 Jeon, Jinho, 06
 Jeong, Changyoung, 2E
 Jiang, Jing, 23
 Johnson, Richard, 0F, 0Y
 Kadoi, Mikio, 27
 Kaiser, Winfried, 0G
 Kamei, Yuya, 26
 Kamohara, Itaru, 0I
 Kandel, Yudhishtir, 0B
 Kaneyama, Koji, 1Z
 Kasahara, Kazuki, 08
 Kawakami, Shinichiro, 0Y, 26
 Kawasuji, Yasufumi, 1J, 2G
 Kazarian, Aram, 1C
 Kazazis, Dimitrios, 25
 Kerkhof, Peter, 1N
 Kiers, Ton, 0H, 15
 Kim, Byung-Hun, 1U
 Kim, Guk-Jin, 1P, 1U, 1V
 Kim, Heebom, 2E
 Kim, Hocheol, 06
 Kim, Hoyeon, 06
 Kim, Hyunwoo, 06
 Kim, In-Seon, 1P, 1U, 1V
 Kim, Insung, 06
 Kim, Jungyeop, 06
 Kim, Min-Su, 1V
 Kim, Muyoung, 2E
 Kim, R. Ryoung-Han, 0H, 0I, 14, 18, 21
 Kim, Seong-Sue, 06
 Kneer, Bernhard, 0G
 Koch, Markus, 0J
 Kocsis, Michael, 1E
 Kodama, Takeshi, 1J, 2G
 Koike, Kyohei, 15
 Kosma, Vasiliki, 08
 Koster, Norbert, 1N
 Krabbendam, Peter, 0G
 Krysak, Marie E., 0Z
 Kubis, Michael, 19
 Kutrzeba Kotowska, Bogumila, 0H, 18
 Kye, Jongwook, 1S
 Lam, Michael, 16
 Larivière, Stéphane, 0H, 18
 Last, Thorsten, 0D, 11
 Latypov, Azat, 2B
 Laubis, Christian, 0P, 10
 Lazzarino, Frederic, 0H, 0R, 18
 Lee, Byunghoon, 2E
 Lee, Donggun, 06
 Lee, Jae Uk, 0L, 21
 Lee, Joe, 1G
 Lee, Seungkoo, 06
 Lee, Siyong, 06
 Lee, Sook, 1E
 Lemley, Corey, 0Y
 Lenderink, Egbert, 0D
 Leray, Philippe, 0H, 18
 Levasier, Leon, 0D
 Levinson, Harry J., 1Y, 2B
 Levinson, Zac, 1W
 Liang, Andrew, 19
 Liang, Chen-Wei, 19
 Liu, Chi-Chun (Charlie), 1A, 1D
 Loopstra, Erik, 0G
 Lucas, Kevin, 1C
 Luong, Kim Vu, 10
 Lyons, Adam, 1E
 Mack, Chris A., 0E
 Mallik, A., 18
 Mangat, Pawitter, 0K, 1T
 Mao, Ming, 0H, 0R, 18
 Marokkey, Sajan, 0B
 Maslow, Mark John, 0H, 15
 Matham, Shravan, 0K
 Matsumoto, Yoko, 27
 Matsunaga, Koichi, 0Y

McClelland, Alexandra L., 0V, 28
 McGeoch, Malcolm W., 2K
 McIntyre, Greg, 0H, 14, 18
 Meeuwissen, Marieke, 0Q, 0T, 23
 Meiling, Hans, 0G
 Meli, Luciana, 0Y, 1D, 1G
 Melvin, Lawrence S., 0B, 0I
 Meyer-Ilse, Julia, 1S
 Meyers, Sheldon, 0F
 Migura, Sascha, 0G
 Mika, Niclas, 0G
 Minami, Yoichi, 27
 Minekawa, Yukie, 29
 Miyakawa, Ryan, 0N
 Mizoguchi, Hakan, 1J, 2G
 Mochi, Iacopo, 0T, 1O, 1Q
 Mohacsi, Istvan, 1O
 Molkenboer, Freek, 1N
 Montgomery, Warren, 28
 Moon, Junghwan, 2E
 Mulwijk, Pim, 1N
 Mulckhuysen, Wouter, 1N
 Murphy, Michael, 09
 Murray, Cody, 0Y
 Muthinti, Raja, 1A
 Na, Jihoon, 06
 Naasz, Sandra, 10
 Nafus, Kathleen, 26
 Nagahara, Seiji, 29
 Nagai, Tomoki, 29
 Nakagawa, Hisashi, 29
 Nakajima, Makoto, 1H
 Nakarai, Hiroaki, 1J, 2G
 Nam, Seok-Woo, 06
 Narasimhan, Amrit, 0W
 Naruoka, Takehiko, 29
 Naulleau, Patrick P., 0M, 0N, 17, 20, 2C
 Natori, Sakurako, 1S
 Neureuther, Andrew R., 0M, 17, 20, 2C
 Nijland, Björn, 1N
 No, Hee-Ra, 1U
 Nowak, Krzysztof M., 1J, 2G
 Ober, Christopher K., 08
 Odent, Jeremy, 08
 Oh, Hye-Keun, 1P, 1U, 1V
 Oh, Taehwan, 1G
 Okamoto, Takeshi, 2G
 Okazaki, Shinji, 1J, 2G
 Oostdijk, Bastiaan, 1N
 Oshima, Akihiro, 29
 Oyama, Kenichi, 1S
 Ozlem, Melih, 13
 Painter, Benjamin, 0B
 Panici, Gianluca, 2I
 Paolillo, S., 18
 Park, Changmin, 06
 Park, Jin-Goo, 1V
 Park, Jinhong, 06
 Park, Joo-On, 06
 Patlolla, Raghuveer, 1A
 Peeters, Rudy, 0D
 Perlitz, Sascha, 0J, 0K
 Petrillo, Karen, 0Y, 1G
 Pflüger, Mika, 0P
 Philipsen, Vicky, 0I, 10
 Pieczulewski, Charles, 1Z
 Pirati, Alberto, 0G
 Pistor, Thomas V., 17
 Pollentier, Ivan, 0L
 Popescu, Carmen, 0V
 Qerimi, Dren, 2I
 Qi, Zhengqing John, 1S, 1Y
 Raghavan, Praveen, 0U
 Raghunathan, Ananthan, 16
 Rajendran, Rajeev, 1O, 1Q
 Raley, Angelique, 1D
 Rankin, Jed, 0K, 13, 1F, 1S, 1Y
 Reddy, Sirish, 19
 Reuter, Christian, 10
 Rio, David, 19, 1E
 Rispens, Gijsbert, 0Q, 0T, 23
 Robinson, Alex P. G., 0V, 28
 Roth, John, 0V, 28
 Rusu, P., 18
 Ruzic, David N., 2I
 Saad, Yves, 0I
 Saitou, Takashi, 1J, 2G
 Sakamoto, Rikimaru, 1H
 Samudrala, Pavan, 0F
 Saulnier, Nicole, 1A, 1G
 Sayan, Safak, 0U
 Schmidt, Kristin, 1D
 Scholze, Frank, 0P, 10
 Sekiguchi, Atsushi, 22, 27
 Seshadri, Indira, 1A, 1D, 1G
 Shamma, Nader, 19
 Shearer, Jefferey C., 1A, 1G
 Shehzad, Atif, 0R
 Sherazi, Y., 18
 Sherwin, Stuart, 17
 Shibayama, Wataru, 1H
 Shigaki, Shuhei, 1H
 Shin, Youngsoo, 2I
 Shiozawa, Takahiro, 26
 Shiraishi, Gosuke, 29
 Shiraishi, Yutaka, 1J, 2G
 Shite, Hideo, 26
 Sieg, Stuart, 1A
 Singh, Lovejeet, 1D, 1G
 Singh, SherJang, 1T
 Singhal, Akhil, 19
 Sizyuk, Tatyana, 2J
 Smith, Bruce W., 1W
 Socha, Robert, 20
 Soltwisch, Victor, 0P
 Souriau, Laurent, 10
 Stamm, Uwe, 0G
 Stoeldraijer, Judon, 0G

Stokes, Harold, 1Z	Xu, Hong, 08
Stowers, Jason K., 1E	Yaegashi, Hidetami, 15
Sun, Lei, 0E, 1G, 1S, 1Y	Yamada, Tsuyoshi, 1J
Tagawa, Seiichi, 29	Yamato, Masatoshi, 15
Takahashi, Seiji, 27	Yamauchi, Shohei, 15
Takeda, Satoshi, 1H	Yamazaki, Taku, 1J, 2G
Tan, L. E., 14, 18	Yan, Qiliang, 0B
Tan, Samantha, 19	Yanagida, Tatsuya, 1J
Tanaka, Hiroshi, 1J, 2G	Yatzor, Brett, 1T
Tanaka, Yuji, 1Z	Yeung, Michael, 1P, 1V
Tasdemir, Zuhdi, 0T	Yildirim, Oktay, 0Q, 0T, 23
Taylor, Ron, 1T	Yoshihara, Kosuke, 29
te Sligte, Edwin, 1N	Yoshitake, Shusuke, 1O, 1Q
Thuring, Bernd, 0G	Yu, Jengyi, 19
Timmermans, Marina, 0L	Zahedmanesh, Houman, 0L
Timoshkov, Vadim, 0H, 15	Zdravkov, Alexander, 0D
Tran, Timothy, 19	Zhang, Yu, 25
Trivkovic, D., 14, 18	Zhang, Yunqiang, 1C
Troost, Kars, 0G	Zhou, Xibin, 1C
Truong, Hoa, 1D	
Turley, Christina, 1F	
Tuttle, Josh, 1C	
Ure, David, 28	
van Adrichem, P., 11	
van Ballegoij, Rob, 0G	
van de Kerkhof, Mark, 0D, 11	
van de Kruijs, Robbert W. E., 10	
Van Den Heuvel, Dieter, 0R	
van der Walle, Peter, 1N	
van Dijk, Joep, 0H	
van Es, Roderik, 0D	
van Oosten, Anton, 0Q	
van Putten, Michel, 1N	
van Schoot, Jan, 0G	
van Schravendijk, Bart, 19	
van Setten, Eelco, 0G	
Vandenberghe, Geert, 0R, 0U	
Vandereyken, Jelle, 19	
Vanelderen, Pieter, 0U	
Verduijn, Erik, 0K, 13	
Vesters, Yannick, 0R, 24	
Viatkina, Katja, 19	
Vockenhuber, Michaela, 09, 0Q, 0T, 25	
Wallow, Thomas L., 1E	
Wan, D., 18	
Wang, Yow-Gwo, 0M, 20	
Ward, Brandon, 19	
Watanabe, Takeo, 22, 27	
Watanabe, Yukio, 1J, 2G	
Westerhout, Jeroen, 1N	
Wiaux, Vincent, 0I	
Wise, Rich, 19	
Wittebrood, Friso, 0H, 11, 18	
Wood, Obert R., 0K, 13, 1S, 1T	
Wu, Lianjia, 0A	
Wuister, Sander, 0Q	
Xiao, Guangming, 1C	
Xu, Dongbo, 10	

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- 1 Keynote Session
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Kenneth A. Goldberg, Lawrence Berkeley National Laboratory
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- 2 EUV Materials I: Metal-Based EUV Resists: Joint Session with
 Conferences 10146 and 10143
Thomas I. Wallow, ASML Brion (United States)
Robert L. Brainard, SUNY CNSE/SUNYIT (United States)
- 3 EUV Materials II: Fundamentals I: Joint Session with Conferences 10146
 and 10143
Clifford L. Henderson, Georgia Institute of Technology (United States)
Anna Lio, Intel Corporation (United States)
- 4 Tutorial Session: Joint Session with Conferences 10143 and 10146
Eric M. Panning, Intel Corporation (United States)
Kenneth A. Goldberg, Lawrence Berkeley National Laboratory
 (United States)
- 5 Integration
Jos P. Benschop, ASML Netherlands B.V. (Netherlands)
Daniel A. Corliss, IBM Corporation (United States)

- 6 EUV Mask Inspection and Imaging: Joint Session with Conferences 10143 and 10145
Anna Tchikoulaeva, Lasertec U.S.A., Inc. Zweigniederlassung Deutschland (Germany)
Ofer Adan, Applied Materials, Ltd. (Israel)
- 7 EUV Optics and Pellicle
Patrick P. Naulleau, Lawrence Berkeley National Laboratory (United States)
Yasin Ekinci, Paul Scherrer Institut (Switzerland)
- 9 Resist Advances and Integration
Robert Bristol, Intel Corporation (United States)
Nelson M. Felix, IBM Corporation (United States)
- 10 Resist Modeling
Thomas I. Wallow, ASML Brion (United States)
Christopher S. Ngai, Applied Materials, Inc. (United States)
- 11 Masks I
Emily E. Gallagher, IMEC (Belgium)
Obert R. Wood II, GLOBALFOUNDRIES Inc. (United States)
- 12 Masks II
Malahat Tarassasoli, Intel Corporation (United States)
Naoya Hayashi, Dai Nippon Printing Company, Ltd. (Japan)
- 13 Patterning I
Soichi Inoue, Toshiba Corporation (Japan)
Bryan S. Kasprowitz, Photonics, Inc. (United States)
- 14 Patterning II
Martin Burkhardt, IBM Thomas J. Watson Research Center (United States)
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- 15 Source
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